

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _C = +25°C T _C = +70°C	I _D	43 34	Α
	Steady State	T _A = +25°C T _A = +70°C	I _D	13.1 10.5	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	90	Α
Avalanche Current (Notes 7) L = 0.1mH			I _{AR}	28	Α
Avalanche Energy (Notes 7) L = 0.1mH			E _{AR}	40	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P_{D}	1.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	78	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	31	°C/W
Total Power Dissipation (Note 6)		P_{D}	2.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	51	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	21	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	4.7	°C/W
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

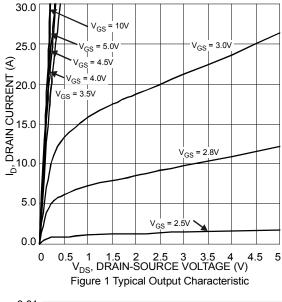
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}		_	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(th)}$	1.0	_	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance			8	9.5	mΩ	$V_{GS} = 10V, I_D = 18A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}		10	11.5	11122	$V_{GS} = 4.5V, I_D = 16A$	
Diode Forward Voltage	V_{SD}	_	0.75	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}		2075			V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss		190		pF		
Reverse Transfer Capacitance	C _{rss}		138				
Gate resistance	R_g		2.4	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg		16.1	_		V _{DS} = 15V, I _D = 18A	
Total Gate Charge (V _{GS} = 10V)	Qg	_	37	_	nC		
Gate-Source Charge	Q_{gs}	_	6.1	_	IIC		
Gate-Drain Charge	Q_{gd}	_	5.9	_		ļ	
Turn-On Delay Time	t _{D(on)}		4.5	_		$V_{DS} = 15V, V_{GS} = 10V,$ $R_{L} = 0.83\Omega, R_{GEN} = 3\Omega,$	
Turn-On Rise Time	t _r	_	19.6	_			
Turn-Off Delay Time	t _{D(off)}		31	_	ns		
Turn-Off Fall Time	t _f	_	10.7	_			
Reverse Recovery Time	t _{rr}	_	13.7	_	ns	1 -45A di/dt-500A/	
Reverse Recovery Charge	Q _{rr}		18.3	_	nC	I _F =15A, di/dt=500A/μs	

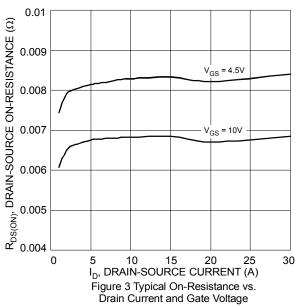
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

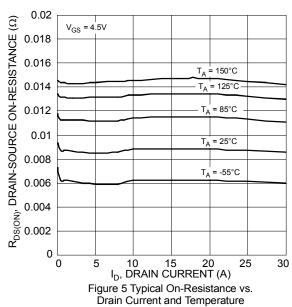
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

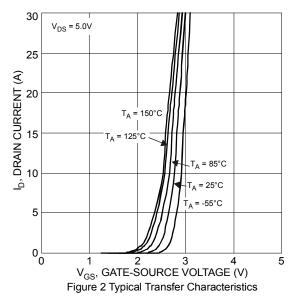
I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

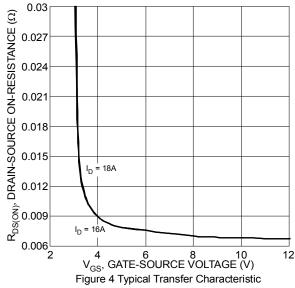


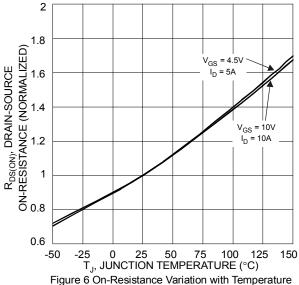




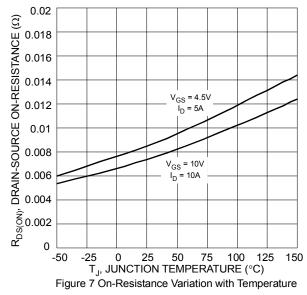


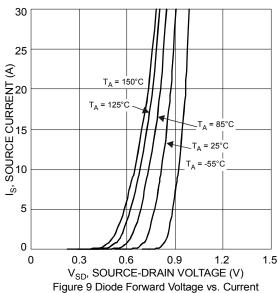


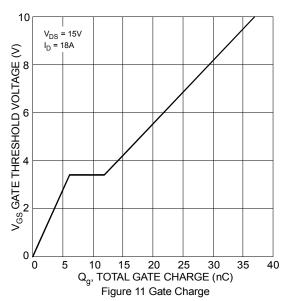












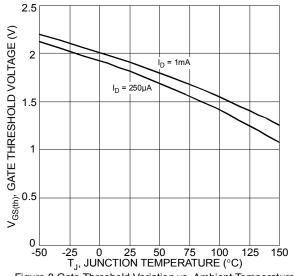
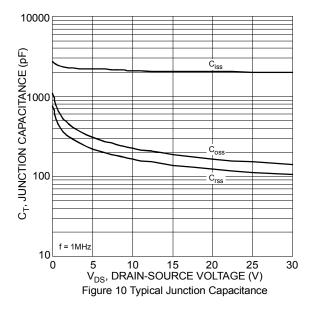
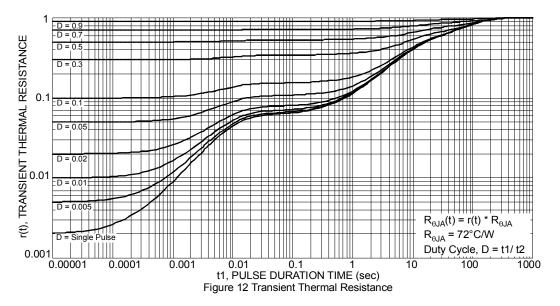


Figure 8 Gate Threshold Variation vs. Ambient Temperature

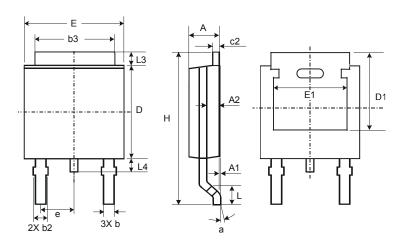






Package Outline Dimensions

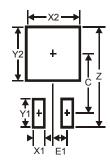
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



TO252						
Dim	Min	Max	Тур			
Α	2.19	2.39	2.29			
A1	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
b	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
c2	0.45	0.58	0.531			
D	6.00	6.20	6.10			
D1	5.21	_	_			
е	Î		2.286			
Е	6.45	6.70	6.58			
E1	4.32	_	_			
Н	9.40	10.41	9.91			
L	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
а	0°	10°	_			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
С	6.9
E1	2.3



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